BUK9K89-100E

Dual N-channel TrenchMOS logic level FET

23 April 2013

Product data sheet

1. General description

Dual logic level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} > 0.5 V @ 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------------------------|----------------------------------|---|--|-----|------|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 100 | V |
| I _D | drain current | V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 12.5 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 38 | W |
| Static characte | eristics FET1 and FET2 | | | | | | , |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 12$ | | - | 75.8 | 89 | mΩ |
| Dynamic characteristics FET1 and FET2 | | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 14; Fig. 15$ | | - | 4.2 | - | nC |



5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1 | S1 | source1 | 8 7 6 5 | D1 D1 D2 D2 |
| 2 | G1 | gate1 | \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\ | |
| 3 | S2 | source2 | | |
| 4 | G2 | gate2 | | |
| 5 | D2 | drain2 | | |
| 6 | D2 | drain2 | O O O | mbk725 |
| 7 | D1 | drain1 | 1 2 3 4 LFPAK56D (SOT1205) | |
| 8 | D1 | drain1 | 2 | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|--------------|----------|--|---------|--|--|
| | Name | Description | Version | | |
| BUK9K89-100E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| BUK9K89-100E | 98910E |

8. Limiting values

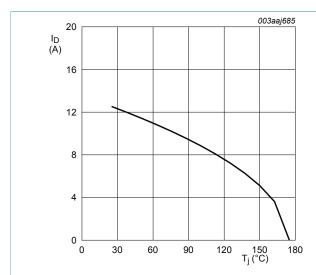
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|-----------------|----------------------|--|--------|-----|------|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 100 | V |
| V_{DGR} | drain-gate voltage | R_{GS} = 20 k Ω ; $T_j \ge 25$ °C; $T_j \le 175$ °C | | - | 100 | V |
| V_{GS} | gate-source voltage | T _j ≤ 175 °C; DC | | -10 | 10 | V |
| | | T _j ≤ 175 °C; Pulsed | [1][2] | -15 | 15 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u> | | - | 12.5 | Α |
| | | T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u> | | - | 8.9 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4 | | - | 50 | Α |

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|--------|-----|------|------|
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 38 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | | - | 260 | °C |
| Source-drai | n diode FET1 and FET2 | | ' | | | |
| I _S | source current | T _{mb} = 25 °C | | - | 12.5 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 50 | Α |
| Avalanche F | Ruggedness FET1 and FET2 | | | | | _ |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 12.5 A; $V_{sup} \le 100 \text{ V}$; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; Fig. 3 | [3][4] | - | 21 | mJ |

- Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- Significantly longer life times are achieved by lowering T_i and or V_{GS} . [2]
- Refer to application note AN10273 for further information
- [3] [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

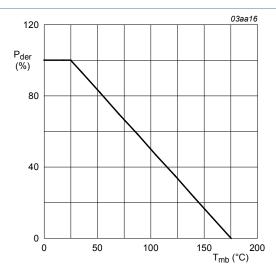


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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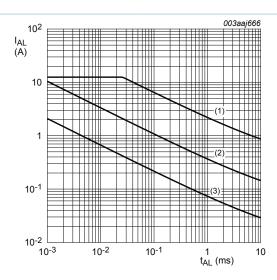


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse; $T_j = 25 \,^{\circ}C$.
- (2) Single-pulse; $T_j = 150 \,^{\circ}C$.
 - (3) Repetitive.

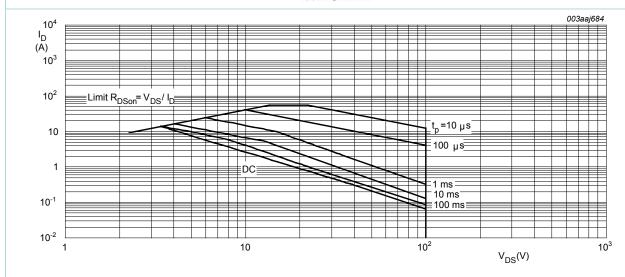


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$$T_{mb} = 25 \,^{\circ}C; I_{DM}$$
 is single pulse

9. Thermal characteristics

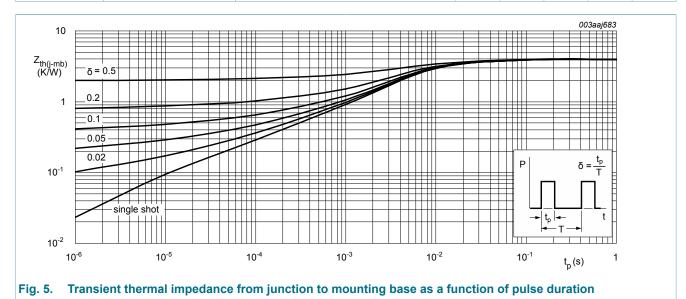
Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--------------------|------------|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance | Fig. 5 | - | - | 3.96 | K/W |
| , | from junction to | | | | | |
| | mounting base | | | | | |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|---|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | Minimum footprint; mounted on a printed circuit board | - | 95 | - | K/W |



10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--|-------------------------------|---|-----|-----------|----------------|----------------|
| Static chara | acteristics FET1 and FET2 | | 1 | | | , |
| V _{(BR)DSS} | drain-source | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 90 | - | - | V |
| | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 100 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11 | 1.4 | 1.7 | 2.1 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11 | 0.5 | - | - | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11 | - | - | 2.45 | V |
| I _{DSS} drain leakage current | drain leakage current | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.02 | 1 | μΑ |
| | | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state | V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u> | - | 75.8 | 89 | mΩ |
| | resistance | V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 12; Fig. 13 | - | 205.4 | 245 | mΩ |
| | | V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; <u>Fig. 12</u> | - | 74.9 | 85 | mΩ |
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------|--|-----|------|------|------|
| Dynamic c | haracteristics FET1 and FE | T2 | | | | |
| Q _{G(tot)} | total gate charge | I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V; | - | 16.8 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u> | - | 1.7 | - | nC |
| Q _{GD} | gate-drain charge | | - | 4.2 | - | nC |
| C _{iss} | input capacitance | V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; | - | 831 | 1108 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 16</u> | - | 81 | 97 | pF |
| C _{rss} | reverse transfer capacitance | | - | 59 | 81 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 80 V; R_{L} = 16 Ω ; V_{GS} = 10 V; | - | 3.6 | - | ns |
| t _r | rise time | $R_{G(ext)} = 10 \Omega; T_j = 25 °C; I_D = 5 A$ | - | 5.8 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 22.1 | - | ns |
| t _f | fall time | | - | 12.1 | - | ns |
| Source-dra | nin diode FET1 and FET2 | 1 | 1 | | 1 | |
| V _{SD} | source-drain voltage | $I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$ | - | 0.78 | 1.2 | ٧ |
| t _{rr} | reverse recovery time | $I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | - | 29.9 | - | ns |
| Q _r | recovered charge | $V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}$ | - | 39.9 | - | nC |

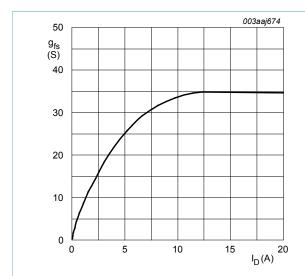


Fig. 6. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$$

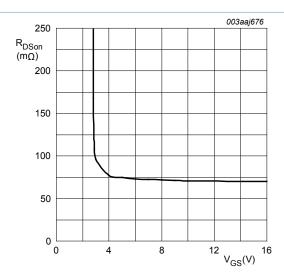


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; \ I_D = 5 A$$

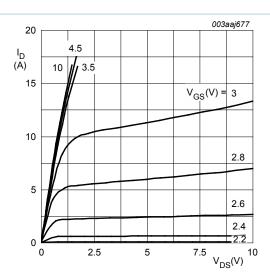


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values



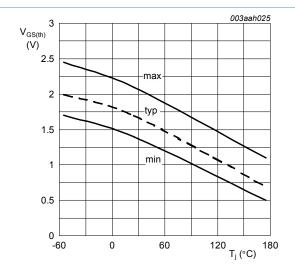


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

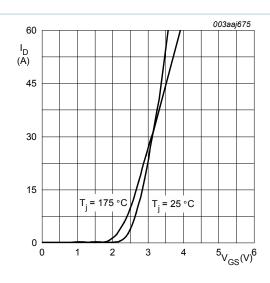


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

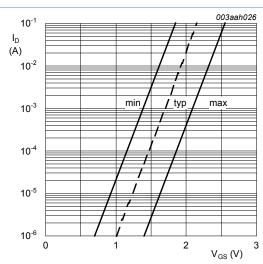


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

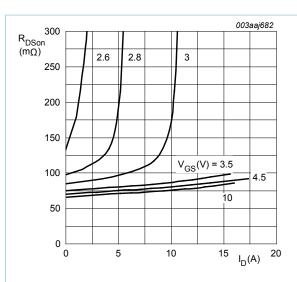


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

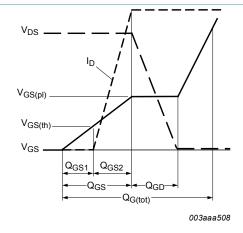


Fig. 14. Gate charge waveform definitions

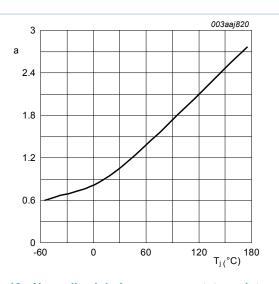


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

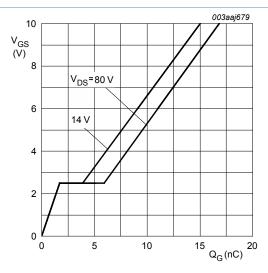


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 5A$$

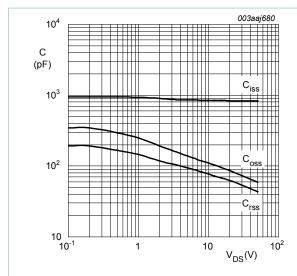
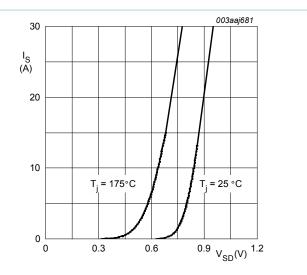


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values

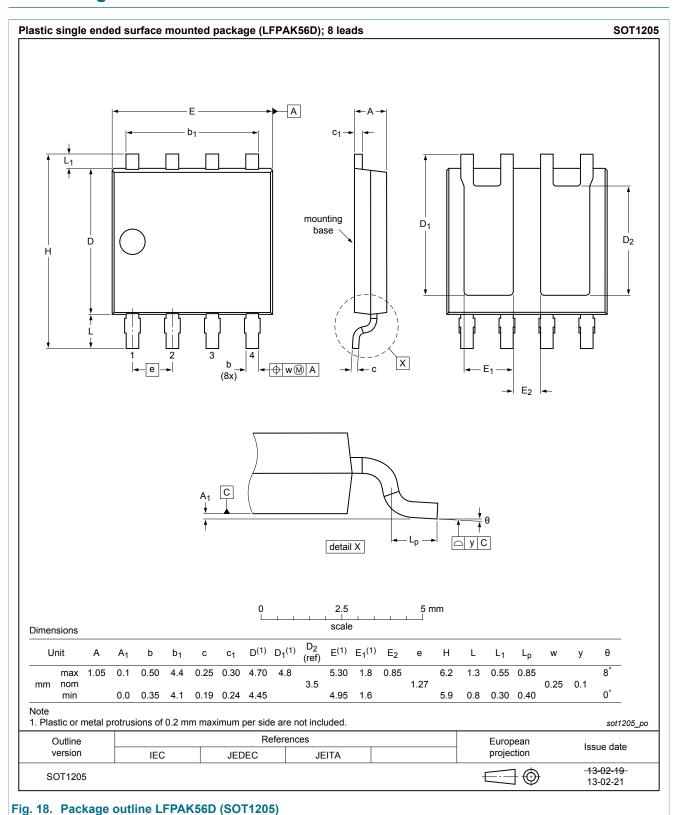
$$V_{GS} = \mathbf{0} V; f = \mathbf{1} M Hz$$



voltage; typical values

$$V_{GS} = 0 V$$

11. Package outline



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12. Legal information

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|--------------------------------------|--------------------|---|
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